

**2N4338
2N4339
2N4340
2N4341**

**CASE 22-03, STYLE 3
TO-18 (TO-206AA)**

**JFET
LOW-FREQUENCY, LOW NOISE**

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	50	Vdc
Drain-Gate Voltage	V_{DG}	50	Vdc
Gate-Source Voltage	V_{GS}	50	Vdc
Reverse Gate-Source Voltage	V_{GSR}	50	Vdc
Gate Current	I_G	50	mA
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.0	mW mW/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +200	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage ($I_G = -1.0 \mu\text{A}$)	$V_{(BR)GSS}$	50	—	Vdc
Gate Reverse Current ($V_{GS} = -30 \text{ V}$)	I_{GSS}	—	0.1	nA
Gate Source Cutoff Voltage ($V_{DS} = 15 \text{ V}$, $I_D = 0.1 \mu\text{A}$)	$V_{GS(off)}$	-0.3 -0.6 -1.0 -2.0	-1.0 -1.8 -3.0 -6.0	Vdc
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ON CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
Zero-Gate-Voltage Drain Current ($V_{DS} = 15 \text{ V}$)	I_{DSS}^*	0.2 0.5 1.2 3.0	0.6 1.5 3.6 9.0	mA
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SMALL-SIGNAL CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
Forward Transfer Admittance ($V_{DS} = 15 \text{ V}$, $f = 1.0 \text{ kHz}$)	$ y_{fs} ^*$	600 800 1300 2000	1800 2400 3000 4000	μmhos
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Output Admittance ($V_{DS} = 15 \text{ V}$, $f = 1.0 \text{ kHz}$)	$ y_{os} $	— — — —	5.0 15 30 60	μmhos
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Input Capacitance ($V_{DS} = 15 \text{ V}$, $f = 1.0 \text{ MHz}$)	C_{iss}	—	6.0	pF
Reverse Transfer Capacitance ($V_{DS} = 15 \text{ V}$, $f = 1.0 \text{ MHz}$)	C_{rss}	—	2.0	pF

FUNCTIONAL CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
Noise Figure ($V_{DS} = 15 \text{ Volts}$, $f = 1.0 \text{ kHz}$, $R_G = 1.0 \text{ M}\Omega$)	NF	—	1.0	dB

*Pulse Test: Pulse Width $\leq 630 \text{ msec}$, Duty Cycle $\leq 10\%$.